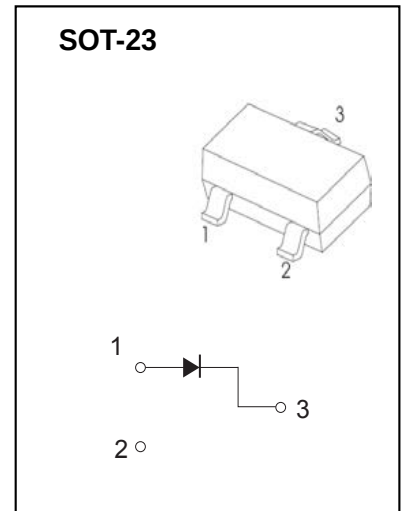
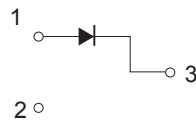
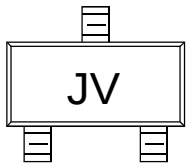


SOT-23 Plastic-Encapsulate Diodes**BAS116****Switching Diodes****FEATURES**

- Medium speed switching times
- Low leakage current applications

MARKING**Equivalent Circuit****MAXIMUM RATINGS** ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

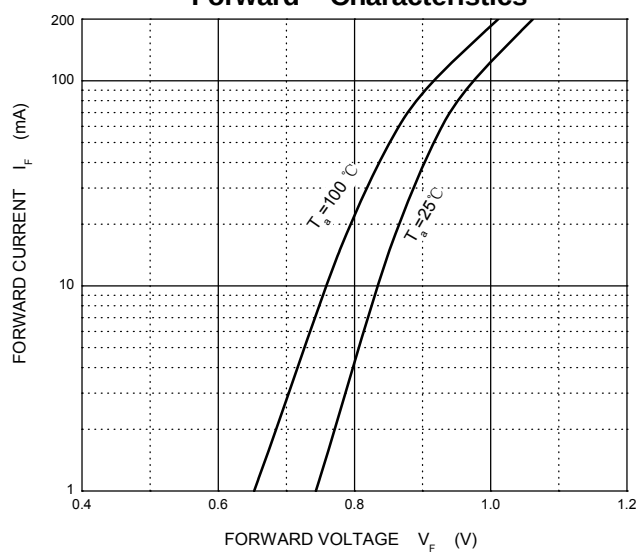
Parameter	Symbol	Limit	Unit
Peak Repetitive Peak Reverse Voltage	V_{RRM}	75	V
Working Peak Reverse Voltage	V_{RWM}		
DC Blocking Voltage	V_R		
Forward Continuous Current	I_{FM}	200	mA
Non-Repetitive Peak Forward Surge Current @ $t=8.3\text{ms}$	I_{FSM}	2.0	A
Power Dissipation	P_D	225	mW
Operation Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

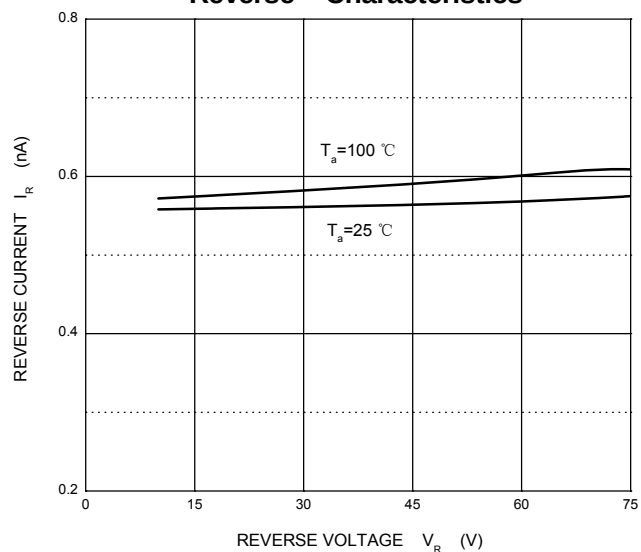
Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Reverse breakdown voltage	$V_{(BR)}$	75			V	$I_R=100\mu\text{A}$
Forward voltage	V_{F1}			0.9	V	$I_F=1\text{mA}$
	V_{F2}			1	V	$I_F=10\text{mA}$
	V_{F3}			1.1	V	$I_F=50\text{mA}$
	V_{F4}			1.25	V	$I_F=150\text{mA}$
Reverse current	I_R			5	nA	$V_R=75\text{V}$
Diode capacitance	C_{tot}		2		pF	$V_R=0\text{V}, f=1\text{MHz}$
Reverse recovery time	t_{rr}			3	μs	$I_F=I_R=10\text{mA}, I_{rr}=0.1 \times I_R, R_L=100\Omega$

Typical Characteristics

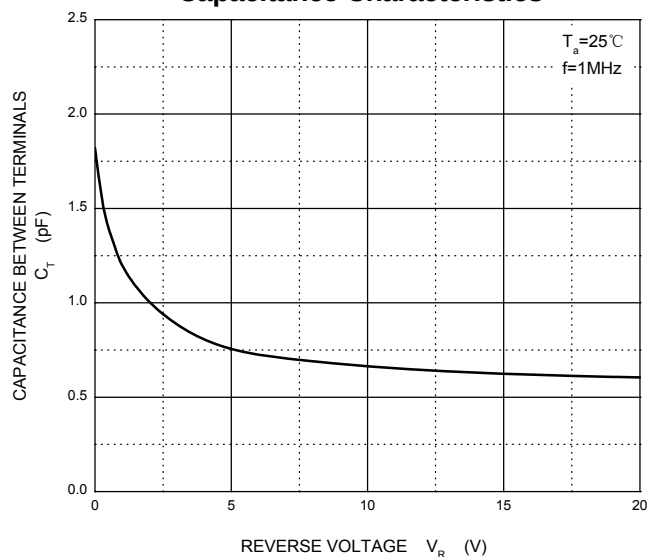
Forward Characteristics



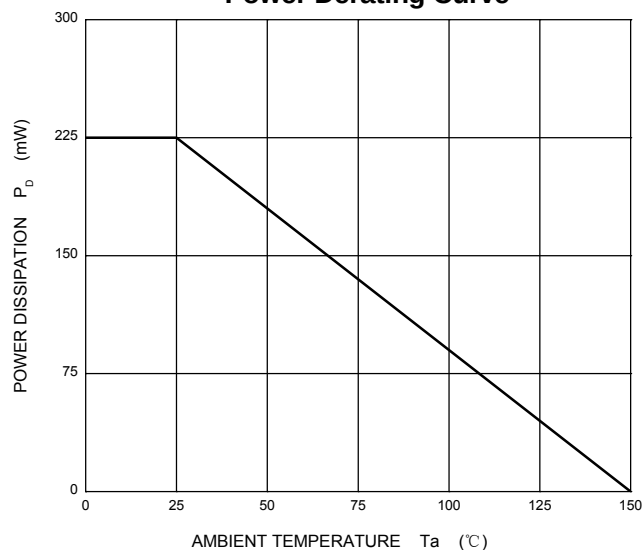
Reverse Characteristics



Capacitance Characteristics



Power Derating Curve



Package Outline Dimensions (SOT-23)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

Suggested Pad Layout (SOT-23)



- Note:
- 1.Controlling dimension:in millimeters.
 - 2.General tolerance:± 0.05mm.
 - 3.The pad layout is for reference purposes only.